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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	09/945507
	Filing Date	August 30, 2001
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2818
	Examiner Name	Unknown
Sheet 1 of 2	Attorney Docket No: 01303.014US1	



US PATENT DOCUMENTS					
Examiner Initials *	Cite No ¹	USP Document No	Publication Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures appear
		US-4412902	11/01/1983	Michikami, Osamu, et al	
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
SN		ARYA, S., "Conduction Properties of Thin Al ₂ O ₃ Films", <u>Thin Solid Films</u> , 91, (1982), pp. 363-374				
SN		DIPERT, BRIAN., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, (October 1993), 48-52				
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SN		GREINER, J.G., "Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma", <u>Journal of Applied Physics</u> , vol. 42, no. 12, (November 1971), 5151-5155				
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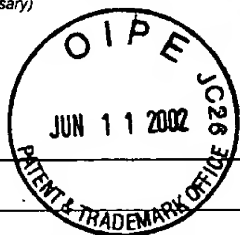
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Attorney Docket No: 01303.014US1

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Examiner Initials*	Cite No ¹	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CA		pp. 125-141	
CA		HURYCH, Z. "Influence of Non-Uniform Thickness of Dielectric Layers on Capacitance and Tunnel Currents", <u>Solid-State Electronics</u> , vol. 9, (1966), 967-979	
		KUBASCHEWSKI, O. "Oxidation of Metals and Alloys", <u>Butterworths</u> , London, (1962), 53-63	
		LUAN, H.F., "High Quality Ta ₂ O ₅ Gate Dielectrics with T _{ox,eq} < 10Å", <u>IEDM Technical Digest</u> , (1999), 141-143	
		MASUOKA, FUJIO., "A 256K flash EEPROM using Triple Polysilicon Technology", 1985 IEEE International Solid-State Circuits Conference. <u>Digest of Technical Papers</u> , (02/1985), 168-169	
		MASUOKA, FUJIO., "A new Flash E ² PROM Cell using Triple Polysilicon Technology", <u>International Electron Devices Meeting. Technical Digest</u> , (12/1984), 464-467	
		MORI, S., "Reliable CVD Inter-Poly Dielectrics for Advanced E&EEPROM", 1985 Symposium on VLSI Technology. <u>Digest of Technical Papers</u> , (1985), 16-17	
		PASHLEY, RICHARD D., "Flash Memories: the best of two worlds", <u>IEEE Spectrum</u> , (December/1989), 30-33	
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		SHI, Y., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (October 1998), pp. 388-390	
CA		SIMMONS, J., "Generalized Formula for the Electric Tunnel Effect between Similar Electrodes Separated by a Thin Insulating Film", <u>Journal of Applied Physics</u> , 34(6), (1963), pp. 1793-1803	
CA		SZE, S., <u>Physics of Semiconductor Devices</u> , Second Edition, (1981), pp. 553-556	

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Substitute Disclosure Statement Form (PTO-1449)

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